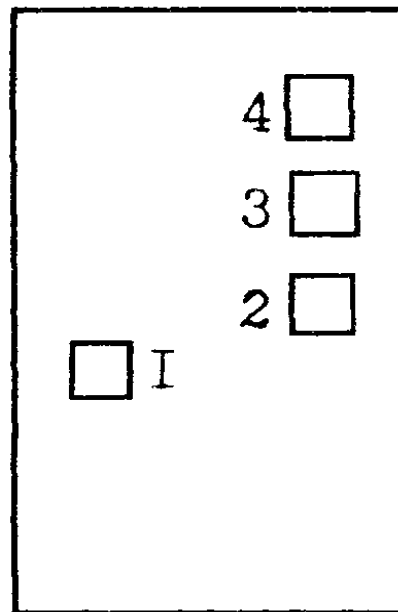




IL2931Z-5 IL2931T-5	Chip for low dropout positive voltage regulator IC
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Features:

- INPUT-TO-OUTPUT VOLTAGE DIFFERENTIAL OF < 0.6V @ 100mA;
- OUTPUT CURRENT IN EXCESS OF 100 mA;
- LOW BIAS CURRENT;
- 60V LOAD DUMP PROTECTION;
- -50V REVERSE TRANSIENT PROTECTION;
- INTERNAL CURRENT LIMITING WITH THERMAL SHUTDOWN;
- IDEALLY SUITED FOR BATTERY POWERED EQUIPMENT



Physical Characteristics:

Wafer Diameter100 ± 0.5 mm
 Wafer thickness 350 ± 20 μm;
 Die size 2.0 x 1.4 mm²;
 Scribe width90 μm

Metallization: Top ... Al – 1.4 ± 0.2 μm
 bottom... Ti-Ni-Ag
 Ti - 0.12 ± 0.02μm
 Ni – 0.5 ± 0.1μm
 Ag – 0.6 ± 0.1μm

Pad #	Characteristics	Bond Pad (μm)	Note	Co-ordinates(bottom left co-ordinates corner), mm		Note
				X	Y	
1	output	180 x 180	- The numbers of Pads are simulated When packing Pads 3 and 4 are to be interconnected	0.070	0.850	Co-ordinates are given co-ordinates on "metallization layer"
2	GNG	180 x 180		1.085	1.200	
3	Input	180 x 180		1.060	1.480	
4	Input	180 x 180		1.060	1.740	

ELECTRICAL CHARACTERISTICS CHIPS ON WAFER

(V_{in}=14V, I_o=10mA, C_i=0.1iF, C_o=100iF, T_j=25°C, (Note 1).)

Characteristic	Symbol	Norm		Unit
		Min	Max	
Output Voltage V _{in} =14V, I _o =10mA V _{in} =6.0V to 26V, I _o ≤100mA.	V _o	4.78 4.55	5.23 5.45	V
Line Regulation V _{in} =9.0V to 16V V _{in} =6.0V to 26V	Reg _{line}	- -	9 29	mV
Load Regulation (I _o =5.0mA to 100mA)	Reg _{load}	-	49	mV
Bias Current V _{in} =14V, I _o =100mA. V _{in} =6.0V to 26V, I _o =10mA.	I _B	- -	27 0.9	mA
Dropout Voltage I _o =10mA I _o =100mA	V _{I-Vo}	- -	0.19 0.58	V
Over-Voltage Shutdown Threshold	V _{th(OV)}	27	39	V
Output Voltage with Reverse Polarity Input (V _{in} =-15V)	-V _o	-0.25	-	V

Note 1: Low duty cycle pulse techniques are used during test to maintain junction temperature as to ambient as possible.